

DTD113Z

NPN SILICON TRANSISTOR

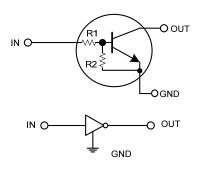
NPN DIGITAL TRANSISTOR (BUILT- IN BIAS RESISTORS)

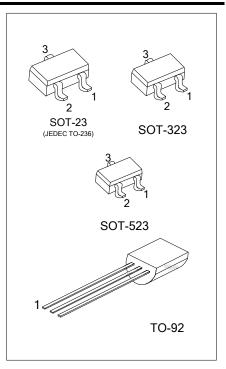
FEATURES

* Built-in bias resistors that implies easy ON/OFF applications.

* The bias resistors are thin-film resistors with complete isolation to allow negative input.

EQUIVALENT CIRCUIT





ORDERING INFORMATION

Ordering Number		Deekege	Pin	Assignr	Decking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	DTD113ZG-AE3-R	SOT-23	G	I	0	Tape Reel	
-	DTD113ZG-AL3-R	DTD113ZG-AL3-R SOT-323 G		I	0	Tape Reel	
-	DTD113ZG-AN3-R	SOT-523	G	I	0	Tape Reel	
DTD113ZL-T92-B	DTD113ZG-T92-B	TO-92	G	0	I	Tape Box	
DTD113ZL-T92-K	DTD113ZG-T92-K	TO-92	G	0	I	Bulk	
Note: Pin Assignment: G		•					

I. IN 0:001 - III Assignment. G. GND

DTD113Z <u>G-AE3-R</u>		(1) B: Tape Box, K: Bulk, R: Tape Reel
	(1)Packing Type (2)Package Type (3)Green Package	 (2) AE3: SOT-23, AL3: SOT-323, AN3: SOT-523, T92:TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free

MARKING

SOT-23 / SOT-323 / SOT-523	TO-92			
	UTC DTD113Z G: Halogen Free Data Code			

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless others specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Supply Voltage		V _{CC}	50	V	
Input Voltage		V _{IN}	-5 ~ +10	V	
Output Current		Ι _{ουτ}	500	mA	
Power Dissipation	SOT-23/SOT-323	P _C	200	mW	
	SOT-523		150	mW	
	TO-92		625	mW	
Junction Temperature		ΤJ	+150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL SPECIFICATIONS (T_A=25°C, unless others specified)

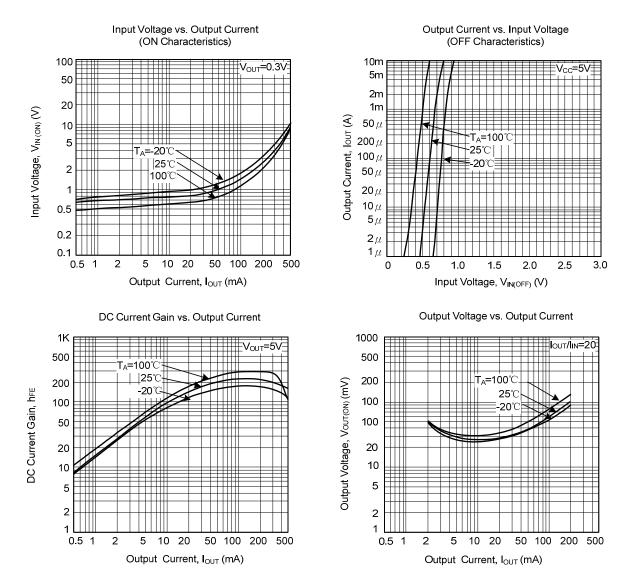
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Voltage	VIN(OFF)	V _{CC} =5V, I _{OUT} =100µA			0.3	v
	V _{IN(ON)}	V _{OUT} =0.3V, I _{OUT} =20mA	1.5			v
Output Voltage	V _{OUT(ON)}	I _{OUT} /I _{IN} =50mA/2.5mA		0.1	0.3	V
Input Current	l _{iN}	V _{IN} =5V			7.2	mA
Output Current	I _{OUT(OFF)}	V _{CC} =50V, V _{IN} =0V			0.5	μA
DC Current Gain	h _{FE}	V _{OUT} =5V, I _{OUT} =50mA	82			
Input Resistance	R ₁		0.7	1	1.3	KΩ
Resistor Ratio	R ₂ /R ₁		8	10	12	
Transition Frequency	f⊤	V _{CE} =10V, I _E =-50mA, f=100MHz (Note)		200		MHz

Note: Transition frequency of the device



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TYPICAL CHARACTERISTICS



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